

Alessandro Paccagnella

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

408
papers

8,882
citations

36
h-index

82
g-index

444
ext. papers

9,973
ext. citations

1.9
avg, IF

5.2
L-index

#	Paper	IF	Citations
408	TID Effects in Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors Irradiated to Ultra-High Doses. <i>IEEE Transactions on Nuclear Science</i> , 2022 , 1-1	1.7	4
407	Energy Deposition by Ultra-High Energy Ions in Large and Small Sensitive Volumes. <i>IEEE Transactions on Nuclear Science</i> , 2022 , 1-1	1.7	
406	Muon detection in electron-positron annihilation for muon collider studies. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2022 , 1024, 166129	1.2	
405	A plug, print & play inkjet printing and impedance-based biosensing technology operating through a smartphone for clinical diagnostics. <i>Biosensors and Bioelectronics</i> , 2022 , 196, 113737	11.8	5
404	DC response, low-frequency noise, and TID-induced mechanisms in 16-nm FinFETs for high-energy physics experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2022 , 166727	1.2	3
403	Secondary Particles Generated by Protons in 3D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2022 , 1-1	1.7	1
402	Increased Device Variability Induced by Total Ionizing Dose in 16 nm Bulk nFinFETs. <i>IEEE Transactions on Nuclear Science</i> , 2022 , 1-1	1.7	2
401	Influence of Fin- and Finger-Number on TID Degradation of 16 nm Bulk FinFETs Irradiated to Ultra-High Doses. <i>IEEE Transactions on Nuclear Science</i> , 2021 , 1-1	1.7	3
400	Depth Dependence of Threshold Voltage Shift in 3-D Flash Memories Exposed to X-Rays. <i>IEEE Transactions on Nuclear Science</i> , 2021 , 68, 659-664	1.7	2
399	A Heavy-Ion Beam Monitor Based on 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2021 , 68, 884-889	1.7	3
398	Inkjet-printed fully customizable and low-cost electrodes matrix for gesture recognition. <i>Scientific Reports</i> , 2021 , 11, 14938	4.9	1
397	TID Degradation Mechanisms in 16-nm Bulk FinFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2021 , 68, 1571-1578	1.7	8
396	Fermi Large Area Telescope Performance after 10 Years of Operation. <i>Astrophysical Journal, Supplement Series</i> , 2021 , 256, 12	8	5
395	Thermal Neutron-Induced SEUs in the LHC Accelerator Environment. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 1412-1420	1.7	6
394	Total-Ionizing-Dose Effects in InGaAs MOSFETs With High-k Gate Dielectrics and InP Substrates. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 1312-1319	1.7	3
393	Characterizing High-Energy Ion Beams With PIPS Detectors. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 1421-1427	1.7	3
392	Ionizing-Radiation Response and Low-Frequency Noise of 28-nm MOSFETs at Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 1302-1311	1.7	15

391	Study of muon pair production from positron annihilation at threshold energy. <i>Journal of Instrumentation</i> , 2020 , 15, P01036-P01036	1	6
390	Total-Ionizing-Dose Effects on InGaAs FinFETs With Modified Gate-stack. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 253-259	1.7	10
389	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO ₂ /Al ₂ O ₃ Dielectrics. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 210-220	1.7	20
388	A Heavy-Ion Detector Based on 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 154-160	1.7	12
387	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 1599-1605	1.7	12
386	Low-Power, Subthreshold Reference Circuits for the Space Environment: Evaluated with β -rays, X-rays, Protons and Heavy Ions. <i>Electronics (Switzerland)</i> , 2019 , 8, 562	2.6	2
385	Charge Buildup and Spatial Distribution of Interface Traps in 65-nm pMOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 1574-1583	1.7	17
384	Inkjet Printed Interdigitated Biosensor for Easy and Rapid Detection of Bacteriophage Contamination: a Preliminary Study for Milk Processing Control Applications. <i>Chemosensors</i> , 2019 , 7, 8	4	11
383	Machine learning on compton event identification for a nano-satellite mission. <i>Experimental Astronomy</i> , 2019 , 47, 129-144	1.3	3
382	Investigating the latent reliability degradation of partially depleted SOI devices induced by high-energy heavy ions irradiation. <i>Microelectronics Reliability</i> , 2019 , 102, 113425	1.2	1
381	Inkjet sensors produced by consumer printers with smartphone impedance readout. <i>Sensing and Bio-Sensing Research</i> , 2019 , 26, 100308	3.3	11
380	A simple and accessible inkjet platform for ultra-short concept-to-prototype sEMG electrodes production. <i>Annual International Conference of the IEEE Engineering in Medicine and Biology Society IEEE Engineering in Medicine and Biology Society Annual International Conference</i> , 2019 , 2019, 5765-5768	0.9	1
379	Total Ionizing Dose Effects in 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 48-53	1.7	20
378	Influence of Halo Implantations on the Total Ionizing Dose Response of 28-nm pMOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 82-90	1.7	18
377	Atmospheric Neutron Soft Errors in 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2019 , 66, 1361-1367	1.7	7
376	The Effect of Proton Irradiation in Suppressing Current Collapse in AlGaIn/GaN High-Electron-Mobility Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 372-377	2.9	10
375	Silver nanoparticles inkjet-printed flexible biosensor for rapid label-free antibiotic detection in milk. <i>Sensors and Actuators B: Chemical</i> , 2019 , 280, 280-289	8.5	49
374	Effects of Heavy-Ion Irradiation on Vertical 3-D NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 318-325	1.7	29

373	Influence of LDD Spacers and H ⁺ Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 164-174	1.7	51
372	Optimization of Cyclic Voltammetric Curve Parameters to Measure Lactate Concentration in Urine Samples. <i>Lecture Notes in Electrical Engineering</i> , 2018 , 103-110	0.2	
371	2018 ,		3
370	Fast neutron irradiation tests of flash memories used in space environment at the ISIS spallation neutron source. <i>AIP Advances</i> , 2018 , 8, 025013	1.5	8
369	Lactate Dehydrogenase and Glutamate Pyruvate Transaminase biosensing strategies for lactate detection on screen-printed sensors. Catalysis efficiency and interference analysis in complex matrices: from cell cultures to sport medicine. <i>Sensing and Bio-Sensing Research</i> , 2018 , 21, 54-64	3.3	9
368	Dose-Rate Sensitivity of 65-nm MOSFETs Exposed to Ultrahigh Doses. <i>IEEE Transactions on Nuclear Science</i> , 2018 , 65, 1482-1487	1.7	19
367	1GigaRad TID impact on 28 nm HEP analog circuits. <i>The Integration VLSI Journal</i> , 2018 , 63, 306-314	1.4	1
366	Upsets in Erased Floating Gate Cells With High-Energy Protons. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 421-426	1.7	1
365	Single Event Upsets Induced by Direct Ionization from Low-Energy Protons in Floating Gate Cells. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 64, 464-470	1.7	12
364	Space and terrestrial radiation effects in flash memories. <i>Semiconductor Science and Technology</i> , 2017 , 32, 033003	1.8	12
363	Space Environment Effects on Flexible, Low-Voltage Organic Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 35150-35158	9.5	13
362	Culture Mediums and Buffer Effect on Screen-printed Carbon Electrodes for Continuous Voltammetric Monitoring of in vitro Cell Cultures Lactate Production. <i>Procedia Technology</i> , 2017 , 27, 246-247		1
361	Total Ionizing Dose effects on a 28 nm Hi-K metal-gate CMOS technology up to 1 Grad. <i>Journal of Instrumentation</i> , 2017 , 12, C02003-C02003	1	13
360	Experimental and Simulation Studies of the Effects of Heavy-Ion Irradiation on HfO ₂ -Based RRAM Cells. <i>IEEE Transactions on Nuclear Science</i> , 2017 , 1-1	1.7	7
359	Total suppression of dynamic-ron in AlGa _N /Ga _N -HEMTs through proton irradiation 2017 ,		7
358	Modeling of SAM Impedance Onto Gold and Silver Thin-Film Mass-Produced Electrodes and Their Use for Optimization of Lactic Acid Detection. <i>IEEE Transactions on Nanobioscience</i> , 2016 , 15, 756-764	3.4	6
357	Muon-induced soft errors in 16-nm NAND flash memories 2016 ,		2
356	Complete loss of functionality and permanent page fails in NAND flash memories 2016 ,		1

355	Comparison of radiation degradation induced by x-ray and 3-MeV protons in 65-nm CMOS transistors. <i>Chinese Physics B</i> , 2016 , 25, 096110	1.2	1
354	Impact of bias conditions on electrical stress and ionizing radiation effects in Si-based TFETs. <i>Solid-State Electronics</i> , 2016 , 115, 146-151	1.7	4
353	Recent progress of RD53 Collaboration towards next generation Pixel Read-Out Chip for HL-LHC. <i>Journal of Instrumentation</i> , 2016 , 11, C12058-C12058	1	12
352	Radiation tolerance study of a commercial 65 nm CMOS technology for high energy physics applications. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2016 , 831, 265-268	1.2	8
351	Single Event Transients and Pulse Quenching Effects in Bandgap Reference Topologies for Space Applications. <i>IEEE Transactions on Nuclear Science</i> , 2016 , 63, 2950-2961	1.7	9
350	Impact of proton fluence on DC and trapping characteristics in InAlN/GaN HEMTs. <i>Solid-State Electronics</i> , 2015 , 113, 15-21	1.7	5
349	Palladium on plastic substrates for plasmonic devices. <i>Sensors</i> , 2015 , 15, 1138-47	3.8	7
348	A subthreshold, low-power, RHBD reference circuit, for earth observation and communication satellites 2015 ,		7
347	Enhancement and control of surface plasmon resonance sensitivity using grating in conical mounting configuration. <i>Optics Letters</i> , 2015 , 40, 221-4	3	8
346	Investigation of Hot Carrier Stress and Constant Voltage Stress in High- κ Si-Based TFETs. <i>IEEE Transactions on Device and Materials Reliability</i> , 2015 , 15, 236-241	1.6	8
345	Comparative study of two measurement/modeling techniques for biodevices functionalization assessment in agri-food applications 2015 ,		1
344	Investigation of total ionizing dose effect and displacement damage in 65 nm CMOS transistors exposed to 3 MeV protons. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2015 , 796, 104-107	1.2	8
343	Impact of Bias Temperature Instability on Soft Error Susceptibility. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2015 , 23, 743-751	2.6	20
342	Radiation Vulnerability in 65 nm CMOS I/O Transistors after Exposure to Grad Dose 2015 ,		1
341	CHIPIX65: Developments on a new generation pixel readout ASIC in CMOS 65 nm for HEP experiments 2015 ,		14
340	Effects of electrical stress and ionizing radiation on Si-based TFETs 2015 ,		1
339	SEE Tests of the NAND Flash Radiation Tolerant Intelligent Memory Stack 2015 ,		2
338	Drain Current Collapse in 65 nm pMOS Transistors After Exposure to Grad Dose. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2899-2905	1.7	16

337	Proton Irradiation Effects on Commercial Laser Diodes 2015 ,		3
336	Sample-to-Sample Variability of Floating Gate Errors Due to Total Ionizing Dose. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2511-2516	1.7	9
335	Enhancement of Transistor-to-Transistor Variability Due to Total Dose Effects in 65-nm MOSFETs. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2398-2403	1.7	26
334	Sensitive Volume and Extreme Shifts in Floating Gate Cells Irradiated with Heavy Ions. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2815-2821	1.7	5
333	Radiation-Induced Short Channel (RISCE) and Narrow Channel (RINCE) Effects in 65 and 130 nm MOSFETs. <i>IEEE Transactions on Nuclear Science</i> , 2015 , 62, 2933-2940	1.7	104
332	Gate Bias Dependence of Defect-Mediated Hot-Carrier Degradation in GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1316-1320	2.9	34
331	Sensitivity of NOR Flash memories to wide-energy spectrum neutrons during accelerated tests 2014 ,		4
330	Heavy-ion induced single event upsets in phase-change memories 2014 ,		1
329	Neutron and Alpha Single Event Upsets in Advanced NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 1799-1805	1.7	12
328	Characterization of Grating Coupled Surface Plasmon Polaritons Using Diffracted Rays Transmittance. <i>Plasmonics</i> , 2014 , 9, 1103-1111	2.4	8
327	Analysis of TID Failure Modes in SRAM-Based FPGA Under Gamma-Ray and Focused Synchrotron X-Ray Irradiation. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 1777-1784	1.7	11
326	Developments on DC/DC converters for the LHC experiment upgrades. <i>Journal of Instrumentation</i> , 2014 , 9, C02017-C02017	1	13
325	Effects of bias on the radiation responses of Si-based TFETs 2014 ,		1
324	Total Ionizing Dose Effects in Si-Based Tunnel FETs. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 2874-2880		11
323	Degradation of dc and pulsed characteristics of InAlN/GaN HEMTs under different proton fluences 2014 ,		2
322	Recoverable degradation of blue InGaN-based light emitting diodes submitted to 3 MeV proton irradiation. <i>Applied Physics Letters</i> , 2014 , 105, 213506	3.4	9
321	Development of a complete plasmonic grating-based sensor and its application for self-assembled monolayer detection. <i>Applied Optics</i> , 2014 , 53, 5969-76	1.7	5
320	Upsets in Phase Change Memories Due to High-LET Heavy Ions Impinging at an Angle. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 3491-3496	1.7	6

319	Sample-to-Sample Variability and Bit Errors Induced by Total Dose in Advanced NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2014 , 61, 2889-2895	1.7	20
318	Radiation Effects in Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 1953-1969	1.7	87
317	Investigation of Supply Current Spikes in Flash Memories Using Ion-Electron Emission Microscopy. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4136-4141	1.7	3
316	Proton-Induced Upsets in SLC and MLC NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4130-4135	1.7	9
315	Effects of high energy x ray and proton irradiation on lead zirconate titanate thin films' dielectric and piezoelectric response. <i>Applied Physics Letters</i> , 2013 , 102, 192906	3.4	19
314	Single and Multiple Cell Upsets in 25-nm NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 2675-2681	1.7	22
313	Coadsorption optimization of DNA in binary self-assembled monolayer on gold electrode for electrochemical detection of oligonucleotide sequences. <i>Journal of Electroanalytical Chemistry</i> , 2013 , 689, 57-62	4.1	7
312	Neutron and alpha SER in advanced NAND Flash memories 2013 ,		1
311	Possible effects on avionics induced by terrestrial gamma-ray flashes. <i>Natural Hazards and Earth System Sciences</i> , 2013 , 13, 1127-1133	3.9	17
310	Temperature dependence of neutron-induced soft errors in SRAMs. <i>Microelectronics Reliability</i> , 2012 , 52, 289-293	1.2	16
309	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2012 , 12, 437-444	1.6	15
308	Radiation Environment in the ITER Neutral Beam Injector Prototype. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 1099-1104	1.7	4
307	Proton-Induced Upsets in 41-nm NAND Floating Gate Cells. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 838-844	1.7	10
306	Retention Errors in 65-nm Floating Gate Cells After Exposure to Heavy Ions. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 2785-2790	1.7	10
305	Degradation of Sub 40-nm NAND Flash Memories Under Total Dose Irradiation. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 2952-2958	1.7	20
304	Alpha-induced soft errors in Floating Gate flash memories 2012 ,		7
303	Power converters for future LHC experiments. <i>Journal of Instrumentation</i> , 2012 , 7, C03012-C03012	1	12
302	Impact of Aging Phenomena on Soft Error Susceptibility 2011 ,		23

301	Electrochemical impedance spectroscopy study of the cells adhesion over microelectrodes array 2011 ,		1
300	Ionizing radiation compatibility in the MITICA neutral beam prototype. <i>Fusion Engineering and Design</i> , 2011 , 86, 1268-1272	1.7	5
299	Single Event Effects in 90-nm Phase Change Memories. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 2755-2760	1.7	13
298	Heavy-Ion Induced Threshold Voltage Shifts in Sub 70-nm Charge-Trap Memory Cells. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 827-833	1.7	5
297	Layout-Aware Multi-Cell Upsets Effects Analysis on TMR Circuits Implemented on SRAM-Based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 2325-2332	1.7	7
296	Effects of Total Ionizing Dose on the Retention of 41-nm NAND Flash Cells. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 2824-2829	1.7	16
295	Impact of Technology Scaling on the Heavy-Ion Upset Cross Section of Multi-Level Floating Gate Cells. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 969-974	1.7	32
294	Angular Dependence of Heavy-Ion Induced Errors in Floating Gate Memories. <i>IEEE Transactions on Nuclear Science</i> , 2011 , 58, 2621-2627	1.7	21
293	Proton-induced upsets in 41-nm NAND floating gate cells 2011 ,		1
292	A study on the short- and long-term effects of X-ray exposure on NAND Flash memories 2011 ,		5
291	FERMI LARGE AREA TELESCOPE FIRST SOURCE CATALOG. <i>Astrophysical Journal, Supplement Series</i> , 2010 , 188, 405-436	8	754
290	Annealing of Heavy-Ion Induced Floating Gate Errors: LET and Feature Size Dependence. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 1835-1841	1.7	32
289	Single Event Gate Rupture in 130-nm CMOS Transistor Arrays Subjected to X-Ray Irradiation. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 1842-1848	1.7	3
288	Heavy-Ion Induced Threshold Voltage Tails in Floating Gate Arrays. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	33
287	Angular and Strain Dependence of Heavy-Ions Induced Degradation in SOI FinFETs. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 1924-1932	1.7	6
286	Increase in the Heavy-Ion Upset Cross Section of Floating Gate Cells Previously Exposed to TID. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	26
285	Impact of Radiation on the Operation and Reliability of Deep Submicron CMOS Technologies. <i>ECS Transactions</i> , 2010 , 27, 39-46	1	2
284	Potential High Resolution Dosimeters For MRT 2010 ,		20

283	Impact of time and space evolution of ion tracks in nonvolatile memory cells approaching nanoscale. <i>Journal of Applied Physics</i> , 2010 , 108, 124907	2.5	6
282	Impact of NBTI Aging on the Single-Event Upset of SRAM Cells. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	14
281	. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 2098-2105	1.7	5
280	Catastrophic Failure in Highly Scaled Commercial NAND Flash Memories. <i>IEEE Transactions on Nuclear Science</i> , 2010 , 57, 266-271	1.7	33
279	Present and Future Non-Volatile Memories for Space. <i>IEEE Transactions on Nuclear Science</i> , 2010 ,	1.7	84
278	Radiation effects on NAND Flash memories 2010 , 537-571		
277	Scaling trends of neutron effects in MLC NAND Flash memories 2010 ,		10
276	Accelerated testing of RF-MEMS contact degradation through radiation sources 2010 ,		2
275	A multi-megarad, radiation hardened by design 512 kbit SRAM in CMOS technology 2010 ,		3
274	Destructive events in NAND Flash memories irradiated with heavy ions. <i>Microelectronics Reliability</i> , 2010 , 50, 1832-1836	1.2	7
273	Impact of total dose on heavy-ion upsets in floating gate arrays. <i>Microelectronics Reliability</i> , 2010 , 50, 1837-1841	1.2	4
272	FERMILARGE AREA TELESCOPE OBSERVATIONS OF THE VELA PULSAR. <i>Astrophysical Journal</i> , 2009 , 696, 1084-1093	4.7	111
271	DfT Reuse for Low-Cost Radiation Testing of SoCs: A Case Study 2009 ,		3
270	Can Atmospheric Neutrons Induce Soft Errors in nand Floating Gate Memories?. <i>IEEE Electron Device Letters</i> , 2009 , 30, 178-180	4.4	9
269	The Role of Irradiation Bias on the Time-Dependent Dielectric Breakdown of 130-nm MOSFETs Exposed to X-rays. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3244-3249	1.7	8
268	Error Instability in Floating Gate Flash Memories Exposed to TID. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3267-3273	1.7	38
267	Heavy Ion Irradiation Effects on Capacitors With SiO_2 and ONO as Dielectrics. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 2218-2224	1.7	6
266	Peculiar characteristics of nanocrystal memory cells programming window. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 512		0

265	Radiation damage on dielectrics: Single event effects. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 406		2
264	Implanted and irradiated SiO ₂ /Bi structure electrical properties at the nanoscale. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 421		1
263	Channel-Hot-Carrier Degradation and Bias Temperature Instabilities in CMOS Inverters. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2155-2159	2.9	15
262	Effects of the Localization of the Charge in Nanocrystal Memory Cells. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2319-2326	2.9	2
261	The on-orbit calibration of the Fermi Large Area Telescope. <i>Astroparticle Physics</i> , 2009 , 32, 193-219	2.4	106
260	Gate dielectric degradation in CMOS inverters. <i>Microelectronic Engineering</i> , 2009 , 86, 2123-2126	2.5	
259	TID Sensitivity of NAND Flash Memory Building Blocks. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 1909-1913	1.7	35
258	A Statistical Approach to Microdose Induced Degradation in FinFET Devices. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3285-3292	1.7	10
257	Evaluating Alpha-induced soft errors in embedded microprocessors 2009 ,		9
256	Methodologies to Study Frequency-Dependent Single Event Effects Sensitivity in Flash-Based FPGAs. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3534-3541	1.7	14
255	Angular and strain dependence of heavy-ions induced degradation in SOI FinFETs 2009 ,		1
254	THE LARGE AREA TELESCOPE ON THE FERMI GAMMA-RAY SPACE TELESCOPE MISSION. <i>Astrophysical Journal</i> , 2009 , 697, 1071-1102	4.7	2463
253	Radiation Sensitivity of Ohmic RF-MEMS Switches for Spatial Applications 2009 ,		11
252	Dose Enhancement Due to Interconnects in Deep-Submicron MOSFETs Exposed to X-Rays. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 2205-2212	1.7	5
251	Gate Rupture in Ultra-Thin Gate Oxides Irradiated With Heavy Ions. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 1964-1970	1.7	11
250	Performance studies of the CMS Strip Tracker before installation. <i>Journal of Instrumentation</i> , 2009 , 4, P06009-P06009	1	2
249	Alignment of the CMS silicon strip tracker during stand-alone commissioning. <i>Journal of Instrumentation</i> , 2009 , 4, T07001-T07001	1	6
248	Channel Hot Carrier Stress on Irradiated 130-nm NMOSFETs. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 1960-1967	1.7	21

247	Total Ionizing Dose Effects on 4 Mbit Phase Change Memory Arrays. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 2090-2097	1.7	11
246	Direct Evidence of Secondary Recoiled Nuclei From High Energy Protons. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 2904-2913	1.7	10
245	Analysis of Proton and Heavy-Ion Irradiation Effects on Phase Change Memories With MOSFET and BJT Selectors. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 3189-3196	1.7	5
244	Gate rupture in ultra-thin gate oxides irradiated with heavy ions 2008 ,		1
243	Neutron-induced soft errors in advanced flash memories 2008 ,		10
242	Effect of Ion Energy on Charge Loss From Floating Gate Memories. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 2042-2047	1.7	13
241	Traces of errors due to single ion in floating gate memories 2008 ,		1
240	Factors impacting the temperature dependence of soft errors in commercial SRAMs 2008 ,		5
239	Microdose and Breakdown Effects Induced by Heavy Ions on Sub 32-nm Triple-Gate SOI FETs. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 3182-3188	1.7	16
238	TID sensitivity of NAND Flash memory building blocks 2008 ,		7
237	On the Evaluation of Radiation-Induced Transient Faults in Flash-Based FPGAs 2008 ,		12
236	Degradation Induced by X-Ray Irradiation and Channel Hot Carrier Stresses in 130-nm NMOSFETs With Enclosed Layout. <i>IEEE Transactions on Nuclear Science</i> , 2008 , 55, 3216-3223	1.7	15
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